

Silicon Carbide Power MOSFET N-Channe Enhancement Mode

Features

- ★ High Blocking Voltage with Low On-Resistance
- ★ High speed switching with low capacitances
- ★ Easy to Parallel and Simple to Drive
- ★ Resistant to Latch-Up
- ★ Halogen Free, RoHS Compliant

Applications

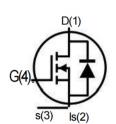
- ★ Solar Inverters
- ★ Switch Mode Power Supplies
- ★ High voltage DC/DC converters
- **★**EV Motor drive

Product Summary

V _{DS}	R _{DS(on)}	I _D @25°		
1200V	13mΩ	167A		







1234

Maximum Ratings (T_C= 25 °C unless otherwise specified)

Parameter	Symbol	Condition	Value	Unit	
Drain-Source Voltage	Vosma	VGs=OV,Io=100uA	1200	V	
Gate-SourceVoltage	V6sm	Absolute maximum values	10/+22	V	
Gate-Source Voltage	VGsop	Recommended operational values	-5/+18	V	
		Vgs=18V,T=25°C	167		
Continuous Drain Current	p	VGs=18V,T=100°C	118	A	
Pulsed Drain Current	oiouse	Pulse widtht, limited by Tma	TBD	A	
Power Dissipation	Ро	T=25°C,T=175°C	555	W	
Operating Junction Temperature	Tvi.op		- 55~175	°C	
Storage Temperature Range	Tstg		55~175	°C	



Electrical Characteristics (Tc=25°C unless otherwise noted)

	01	Condition		Value			
Parameter	Symbo			Min	Тур.	Max	Unit
Drain-Source Breakdown Voltage	VB)pss	VGs=OV,Io=100 μ A		1200			V
Gate Threshold Voltage	VGsth)	Vos=V ₆ g o=20mA	T=25°C		2.9		V
			T=175°C		2.1		
Zero Gate Voltage Drain Current	loss	Vos=1200V,Vss=0V			1	100	μА
Gate-Source Leakage Current	IGss	VGs=18V,Vos=0V			1	100	nA
Dunin Courses On State Desigton on	Roson)	VGs=18V,Io=75A	Tw=25℃		13		mQ
Drain-Source On-State Resistance	1(05011)	VGS=16V,10=75A	T=175°C		20		IIIQ
Turner	Bs	Vos=20V,Ios=75A	Ty=25°C		TBD		S
Transconductance	DS	V05-20 V,105-70A	Tv=175°C		TBD		3
Input Capacitance	Ciss				3815		
Output Capacitance	Cos	VGs=0V			239		pF
Reverse Transfer Capacitance	Cs	Vos=1200 V f=100KHz VAc=25m V			29		1
Coss Stored Energy	Eoss				TBD		μ
			Ty=25°C		TBD		
Turn-On Switching Energy	EoN	Vos=800V,Vgs=-5/18V	T=175°C		TBD		
T Off C'. 1.' P		o=75A,Rg(ext=2.5Q, L=250 μ H	T=25°C		TBD		μ
Turn Off Switching Energy	Eor		T=175°C		TBD		
Turn-On DelayTime	td(onl				TBD		
Rise Time	t	Vos=800V,Vgs=-5/18V lo=75A,RG(ext)=2.5Q,			TBD		
Tumn-Off Delay Time	tdloff)	T=25°C,L=250 μ H Timingrelative to Vos			TBD		ns
Fall Time	t				TBD		
Internal Gate Resistance	RGint)	f=1MHz,VAc=25mV			TBD		Q
Gate to Source Charge	Q				46		
Gate to Drain Charge	Qg	Vos=800V,Vgs=-5/18V o=75A			100		nC
TotalGate Charge	Qg				216		



Body Diode Characteristics (Ty=25°Cunless otherwise noted)

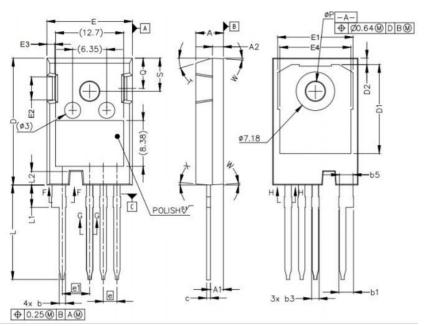
	0-11			Value			·
Parameter	Symbol	Condition		Min	Тур.	Max	Unit
Diada Ramand Waltaga			T=25°C		4.7		***
Diode Forward Voltage	Vso	Vcs=-5V,Iso=37.5A	Tv=175°C		4.1		V
Continuous Diode Forward Current	ls	VGs=-5V,Tc=25°C				TBD	A
Diode Pulse Current	stpuse)	Vgs=-5V,Pulse width t,limite	ed by Tjmax			TBD	A
Reverse Recovery Time	t	VGs=-5V			TBD		ns
Reverse Recovery Charge	Q	so=37.5A RGfea)=2.50 T=175°C			TBD		nC
Peak Reverse Recovery Current	m	VR=800V			TBD		A

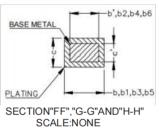
Thermal Characteristics

			Value			
Parameter	Symbol	Condition	Min	Тур.	Max	Unit
ThermalResistance:Junction to Case	Rth(-C			0.27	0.37	°C/W



Outline Drawing





orn en or	MILLIMETERS			
SYMBOL	MIN	MAX		
A	4.83	5.21		
A1	2.29	2.54		
A2	1.91	2.16		
b	1.07	1.28		
b	1.07	1.33		
b1	2.39	2.94		
b2	2.39	2.84		
b3	1.07	1.60		
b4	1.07	1.50		
b5	2.39	2.69		
b6	2.39	2.64		
С	0.55	0.65		
С	0.55	0.68		
D	23.30	23.60		
D1	16.25	17.65		
D2	0.95	1.25		
Е	15.75	16.13		
E1	13.10	14.15		
E2	3.68	5.10		
E3	1.00	1.90		
E4	12.38	13.43		
е	2.54			
e1	5.08	BSC		
N		4		
L	17.31	17.82		
L1	3.97	4.37		
L2	2.35	2.65		
οP	3.51	3.65		
Q	5.49	6.00		
S	6.04	6.30		
	17.5 REF.			
W	3.5 ° REF.			
X	4°)	REF		

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